# RENESAS HD74LVC2244A

## Octal Buffers / Line Drivers with 3-state Outputs

REJ03D0376-0300 (Previous ADE-205-234A (Z)) Rev.3.00 Aug. 20, 2004

### Description

The HD74LVC2244A has eight line drivers with three state outputs in a 20 pin package. This device is a noninverting buffer and has two active low enables ( $1\overline{G}$  and  $2\overline{G}$ ). Each enable independently controls four buffers.

All outputs, which are designed to sink up to 12mA, include equivalent 26  $\Omega$  resistors to reduce overshoot and undershoot.

Low voltage and high-speed operation is suitable at battery drive product (note type personal computer) and low power consumption extends the life of a battery for long time operation.

#### Features

- $V_{CC} = 1.65$  to 5.5 V
- All inputs  $V_{IH}$  (Max) = 5.5 V (@V<sub>CC</sub> = 0 to 5.5 V)
- All outputs  $V_0$  (Max) = 5.5 V (@V<sub>CC</sub> = 0 V or output off state)
- Typical  $V_{OL}$  ground bounce < 0.8 V (@V<sub>CC</sub> = 3.3 V, Ta = 25°C)
- Typical  $V_{OH}$  undershoot > 2.0 V (@V<sub>CC</sub> = 3.3 V, Ta = 25°C)
- High output current  $\pm 12$ mA (@V<sub>CC</sub> = 3.0 to 5.5 V)
- All outputs have equivalent 26  $\Omega$  series resistors, so no external resistors are required
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)		
HD74LVC2244AFPEL	SOP-20 pin (JEITA)	FP-20DAV	FP	EL (2,000 pcs/reel)		
HD74LVC2244ATELL	TSSOP-20 pin	TTP-20DAV	Т	ELL (2,000 pcs/reel)		

Note: Please consult the sales office for the above package availability.

### **Function Table**

#### Inputs

G	Α	Output Y
Н	Х	Z
L	Н	Н
L	L	L

H: High level

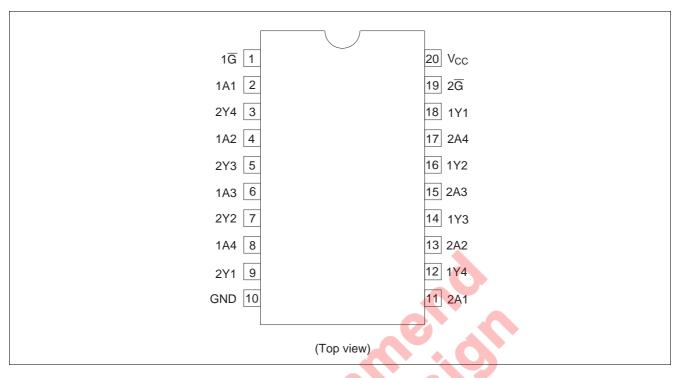
L: Low level

X: Immaterial

Z: High impedance



### **Pin Arrangement**



### **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V <sub>CC</sub>	-0.5 to 7.0	V	
Input voltage	VI	-0.5 to 7.0	V	
Output voltage	Vo 🧹	-0.5 to 7.0	V	Output "Z" or V <sub>CC</sub> : OFF
		–0.5 to V <sub>CC</sub> +0.5		Output "H" or "L"
Input diode current	I <sub>IK</sub>	-50	mA	V <sub>1</sub> < 0
Output diode current	Іок	-50	mA	V <sub>O</sub> < 0
Output current	lo	±50	mA	
V <sub>CC</sub> , GND current	I <sub>CC</sub> or I <sub>GND</sub>	±100	mA	
Storage temperature	Tstg	–65 to 150	°C	

Note: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore no two of which may be realized at the same time.

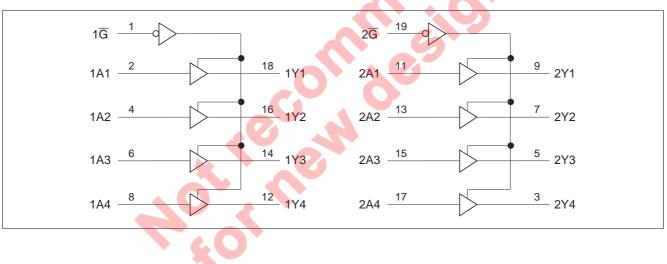
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Recommended Operating Conditions								
Item	Symbol	Ratings	Unit	Conditions				
Supply voltage	V <sub>CC</sub>	1.65 to 5.5	V	At operation				
		1.5 to 5.5		Data retention only				
Input voltage	VI	0 to 5.5	V					
Output voltage	Vo	0 to 5.5	V	Output "Z" or V <sub>CC</sub> : OFF				
		0 to V <sub>CC</sub>		Output "H" or "L"				
Output current	I <sub>OH</sub>	-2	mA	$V_{CC} = 1.65 V$				
		-4		$V_{CC} = 2.3 V$				
		-8		$V_{CC} = 2.7 V$				
		-12		$V_{CC}$ = 3.0 to 5.5 V				
	I <sub>OL</sub>	2	mA	V <sub>CC</sub> = 1.65 V				
		4		$V_{CC} = 2.3 V$				

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		4		$V_{CC} = 2.3 V$
		8		V <sub>CC</sub> = 2.7 V
		12		$V_{CC} = 3.0$ to 5.5 V
Input rise / fall time	t <sub>r</sub> , t <sub>f</sub>	0 to 6	ns / V	
Operating temperature	Та	-40 to +85	°C	

### Logic Diagram



### **Electrical Characteristics**

ltem	Symbol	V <sub>cc</sub> (V)	Min	Тур	Max	Unit	Test Conditions
Input voltage	VIH	1.65 to 1.95	V <sub>CC</sub> ×0.65		_	V	
		2.3 to 2.7	1.7	_	_		
		2.7 to 3.6	2.0	_	_		
		4.5 to 5.5	V <sub>CC</sub> ×0.7	_	_		
	V <sub>IL</sub>	1.65 to 1.95	_	_	V <sub>CC</sub> ×0.35	V	
		2.3 to 2.7	_	_	0.7		
		2.7 to 3.6	_	_	0.8		
		4.5 to 5.5	_	_	V <sub>CC</sub> ×0.3		
Output voltage	V <sub>OH</sub>	1.65 to 5.5	V <sub>CC</sub> -0.2	_	_	V	I <sub>OH</sub> = -100 μA
		1.65	1.2	_	_		$I_{OH} = -2 \text{ mA}$
		2.3	1.7	_	_		$I_{OH} = -4 \text{ mA}$
		2.7	2.2	_	_		
		3.0	2.4	_	_	$\bigcirc$	I <sub>OH</sub> = -6 mA
		2.7	2.0	_	-		I <sub>OH</sub> = -8 mA
		3.0	2.0	_	-		I <sub>он</sub> = –12 mA
		4.5	3.6	_			
	Vol	1.65 to 5.5	_	-	0.2	V	I <sub>OL</sub> = 100 μA
		1.65	_	-	0.45		$I_{OL} = 2 \text{ mA}$
		2.3	_	-	0.7		$I_{OL} = 4 \text{ mA}$
		2.7	—		0.4		
		3.0	-	-	0.55		I <sub>OL</sub> = 6 mA
		2.7	-	/_ (	0.6		I <sub>OL</sub> = 8 mA
		3.0		-	0.8		I <sub>OL</sub> = 12 mA
		4.5	4	-	0.8		
Input current	l <sub>iN</sub>	0 to 5.5	-		±5	μΑ	$V_{IN} = 0$ to 5.5 V
Off state output	loz	1.65 to 5.5	- K	—	±5	μΑ	$V_{OUT} = 0$ to 5.5 V
current							
Output leak current	IOFF	0	`	—	±5	μΑ	$V_{IN}$ or $V_O = 5.5 V$
Quiescent supply	lcc	1.65 to 3.6	_	—	10	μΑ	$V_{IN} = 3.6$ to 5.5 V <sup>*1</sup> , $I_0 = 0$
current		1.65 to 5.5	_	_	10		$V_{IN} = V_{CC} \text{ or } GND$
	Δlcc	2.7 to 3.6	—	—	500	μΑ	$V_{IN}$ = one input at (V <sub>CC</sub> -0.6)V,
							other inputs at $V_{\text{CC}}$ or GND
Input capacitance	C <sub>IN</sub>	3.3	_	3.4	_	pF	$V_{IN} = V_{CC}$ or GND
Output capacitance	Co	3.3	_	9.0	_	pF	$V_{OUT} = V_{CC} \text{ or } GND$

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 $(Ta = -40 \text{ to } 85^{\circ}C)$ 

Note: 1. This applies in the disabled state only.

### **Switching Characteristics**

							(T	$a = -40 \text{ to } 85^{\circ}\text{C}$
							FROM	то
ltem	Symbol	V <sub>cc</sub> (V)	Min	Тур	Max	Unit	(Input)	(Output)
Propagation delay time	t <sub>PLH</sub>	1.8±0.15	_	_	10.5	ns	А	Y
	t <sub>PHL</sub>	2.5±0.2	_	_	7.0			
		2.7	—	—	6.4			
		3.3±0.3	1.5	_	5.5			
		5.0±0.5		_	4.1			
Output enable time	t <sub>ZH</sub>	1.8±0.15	_	_	13.0	ns	G	Y
	t <sub>ZL</sub>	2.5±0.2	_	_	9.0			
		2.7			8.1			
		3.3±0.3	1.0		7.1			
		5.0±0.5	_	—	5.6			
Output disable time	t <sub>HZ</sub>	1.8±0.15	_	_	10.0	ns	G	Y
	t <sub>LZ</sub>	2.5±0.2	_	_	8.0			
		2.7	_	_	7.3			
		3.3±0.3	1.5		6.8			
		5.0±0.5			5.7			
Between output pin skew **	t <sub>OSLH</sub>	1.8±0.15	_	_	2.0	ns		
	toshL	2.5±0.2	—		2.0			
		2.7			1.5			
		3.3±0.3	_	A	1.0			
		5.0±0.5	-		1.0			

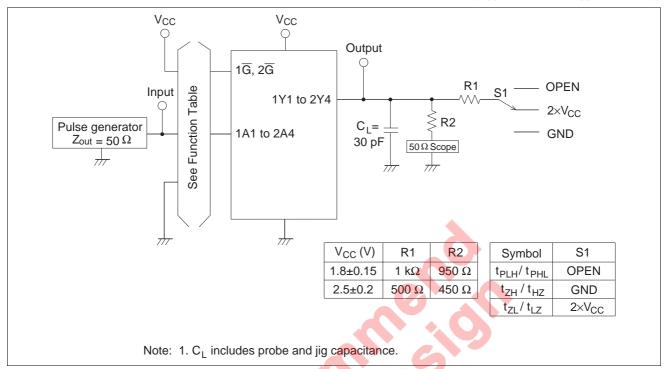
Note: 1. This parameter is characterized but not tested.

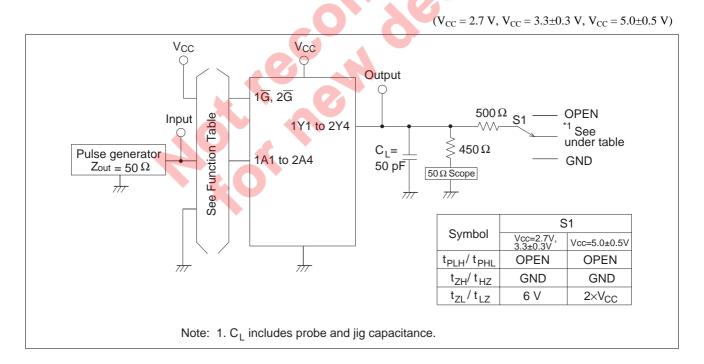
t<sub>oslh</sub> = |t<sub>plhm</sub>-t<sub>plhn</sub>|, t<sub>oshl</sub> = |t<sub>phlm</sub>-t<sub>phln</sub>|



### **Test Circuit**

 $(V_{CC} = 1.8 \pm 0.15 \text{ V}, V_{CC} = 2.5 \pm 0.2 \text{ V})$ 

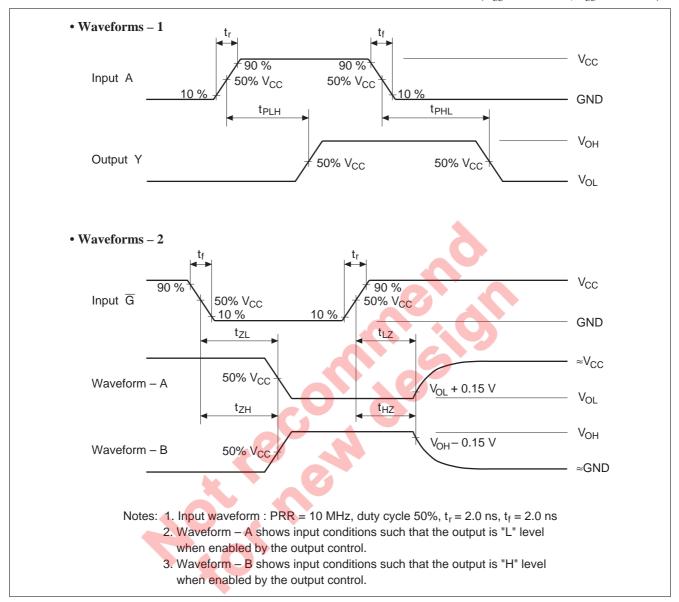




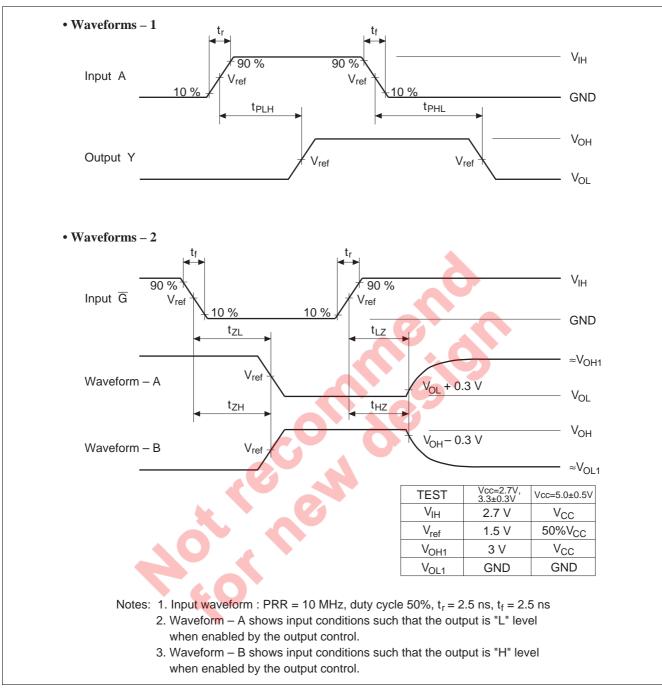


#### Waveforms

 $(V_{CC} = 1.8 \pm 0.15 \text{ V}, V_{CC} = 2.5 \pm 0.2 \text{ V})$ 

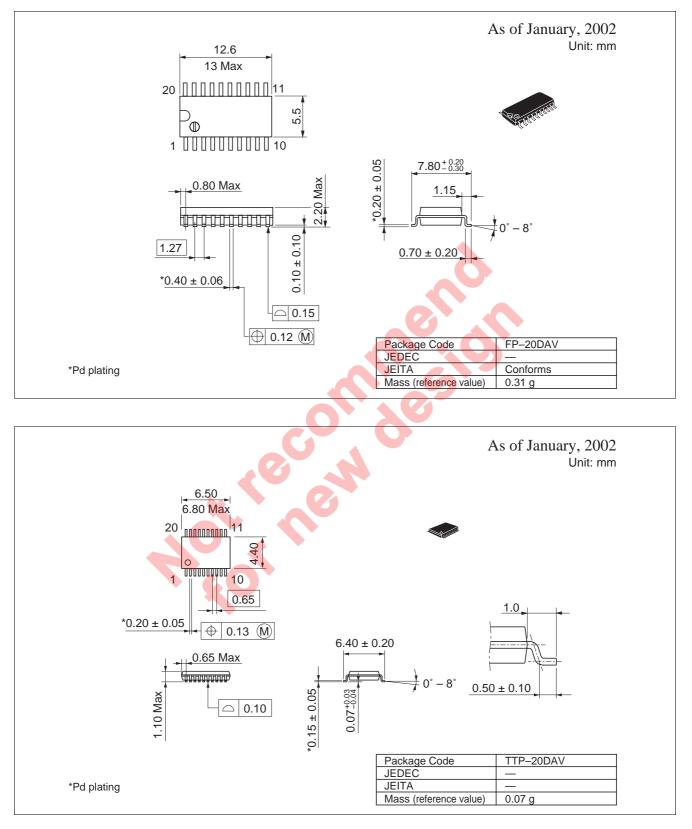






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### **Package Dimensions**



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